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| <ul> <li>Meets or Exceeds the Requirements of<br/>TIA/EIA-232-F and ITU Recommendation<br/>V.28</li> </ul>   | DW OR N PACKAGE<br>(TOP VIEW)                                  |  |  |
|--|--|--|--|
| <ul> <li>Single Chip With Easy Interface Between<br/>UART and Serial-Port Connector</li> </ul>               | V <sub>DD</sub> [ 1 20] V <sub>CC</sub><br>RA1 [ 2 19] RY1     |  |  |
| <ul> <li>Less Than 9-mW Power Consumption</li> <li>Wide Driver Supply Voltage 4.5 V to<br/>13.2 V</li> </ul> | RA2 [] 3 18 ] RY2<br>RA3 [] 4 17 ] RY3<br>DY1 [] 5 16 ] DA1    |  |  |
| <ul> <li>Driver Output Slew Rate Limited to<br/>30 V/µs Max</li> </ul>                                       | DY2 [] 6 15 ]] DA2<br>RA4 [] 7 14 ]] RY4<br>DY3 [] 8 13 ]] DA3 |  |  |
| <ul> <li>Receiver Input Hysteresis 1100 mV Typ</li> <li>Push-Pull Receiver Outputs</li> </ul>                | RA5 [ 9 12 ] RY5<br>V <sub>SS</sub> [ 10 11 ] GND              |  |  |
| <ul> <li>On-Chip Receiver 1-μs Noise Filter</li> </ul>   |  |  |  |

- Functionally Interchangeable With Texas Instruments SN75185
- Operates Up to 120 kbit/s Over a 3-Meter Cable (See Application Information for Conditions)

#### description

The SN75C185 is a low-power BiMOS device containing three independent drivers and five receivers that are used to interface data terminal equipment (DTE) with data circuit-terminating equipment (DCE). Typically, the SN75C185 replaces one SN75188 and two SN75189 devices. This device conforms to TIA/EIA-232-F. The drivers and receivers of the SN75C185 are similar to those of the SN75C188 and SN75C189A, respectively. The drivers have a controlled output slew rate that is limited to a maximum of 30 V/ $\mu$ s, and the receivers have filters that reject input noise pulses that are shorter than 1  $\mu$ s. Both these features eliminate the need for external components.

The SN75C185 uses the low-power BiMOS technology. In most applications, the receivers contained in this device interface to single inputs of peripheral devices such as ACEs, UARTS, or microprocessors. By using sampling, such peripheral devices usually are insensitive to the transition times of the input signals. If this is not the case, or for other uses, it is recommended that the SN75C185 receiver outputs be buffered by single Schmitt input gates or single gates of the HCMOS, ALS, or 74F logic families.

The SN75C185 is characterized for operation from 0°C to 70°C.



Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

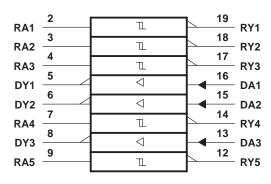
PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.



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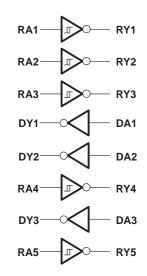
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## logic symbol<sup>†</sup>



<sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

logic diagram (positive logic)





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Output

DΫ́

GND

Vss

Output RY

## EQUIVALENT DRIVER INPUT EQUIVALENT DRIVER OUTPUT VDD VDD Input Internal DA 1.4-V Ref to GND **160** Ω $\mathcal{N}$ **74** Ω GND VSS **72** Ω EQUIVALENT RECEIVER INPUT EQUIVALENT RECEIVER OUTPUT Vcc Input ŔΑ **3.4 k**Ω ESD Protection **1.5 k**Ω ESD Protection ≶ **530 k**Ω ►

## equivalent schematics of inputs and outputs

All resistor values are nominal.



GND

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#### absolute maximum ratings over operating free-air temperature range (unless otherwise noted)<sup>†</sup>

| $\begin{array}{c} -13.5 \ V \\7 \ V \\7 \ V_{SS} \text{ to } V_{DD} \\7 \ V_{SS} \text{ to } V_{DD} \\7 \ V_{SS} \text{ to } V_{DD} \\7 \ V_{SS} - 6 \ V \text{ to } V_{DD} + 6 \ V \\7 \ V_{SS} - 6 \ V \text{ to } V_{CC} + 0.3 \ V \\7 \ S8^{\circ} C/W \\69^{\circ} C/W \end{array}$ |
|--|
|  |

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. All voltages are with respect to network GND.

2. The package thermal impedance is calculated in accordance with JESD 51.

#### recommended operating conditions

|                |                                |                 | MIN                | NOM | MAX             | UNIT |
|----------------|--------------------------------|-----------------|--------------------|-----|-----------------|------|
|                |                                | V <sub>DD</sub> | 4.5                | 12  | 13.2            | V    |
|                | Supply voltage                 | VSS             | -4.5               | -12 | -13.2           | V    |
|                |                                | VCC             | 4.5                | 5   | 6               | V    |
| VI             | Input voltage (see Note 3)     | Drivers         | V <sub>SS</sub> +2 |     | V <sub>DD</sub> | v    |
|                |                                | Receivers       | -25                |     | 25              |      |
| VIH            | High-level input voltage       | Drivers         | 2                  |     |                 | V    |
| VIL            | Low-level input voltage        | Drivers         |                    |     | 0.8             | V    |
| ЮН             | High-level output current      | Dessiver        |                    |     | -1              | mA   |
| IOL            | High-level output current      | Receivers       |                    |     | 3.2             | mA   |
| т <sub>А</sub> | Operating free-air temperature | •               | 0                  |     | 70              | °C   |

NOTE 3: The algebraic convention, where the more positive (less negative) limit is designated as maximum, is used in this data sheet for logic levels only, e.g., if -10 V is a maximum, the typical value is a more negative voltage.

#### supply currents

|                 | PARAMETER                   | TEST CONDITIONS                        |                         |                  | MIN | TYP  | MAX  | UNIT |
|-----------------|-----------------------------|--|-------------------------|------------------|-----|------|------|------|
| inn             | Supply current from Voo     | V <sub>DD</sub> = 5 V,                 | $V_{SS} = -5 V$         |                  | 115 | 200  | μA   |      |
| <sup>I</sup> DD | Supply current norm vDD     | All inputs at 2 V or 0.8 V             | V <sub>DD</sub> = 12 V, | $V_{SS} = -12 V$ |     | 115  | 200  | μΑ   |
|                 | Supply current from VSS     | No load,<br>All inputs at 2 V or 0.8 V | V <sub>DD</sub> = 5 V,  | $V_{SS} = -5 V$  |     | -115 | -200 | μA   |
| ISS             | Supply current norm VSS     |  | V <sub>DD</sub> = 12 V, | $V_{SS} = -12 V$ |     | -115 | -200 | μΑ   |
|                 | Supply current from Vee     | No load                                | V <sub>DD</sub> = 5 V,  | $V_{SS} = -5 V$  |     |      | 750  | μA   |
| CC              | ICC Supply current from VCC | V <sub>DD</sub> = 12 V,                | $V_{SS} = -12 V$        |                  |     | 750  | μΑ   |      |



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### DRIVER SECTION

# electrical characteristics over operating free-air temperature range, $V_{DD}$ = 12 V, $V_{SS}$ = –12 V, $V_{CC}$ = 5 V $\pm 10\%$ (unless otherwise noted)

|                 | PARAMETER  |  | TEST CONDITIONS   |                        |                  | MIN | TYP†  | MAX | UNIT |
|-----------------|--|--|---|------------------------|------------------|-----|-------|-----|------|
| Vall            | High-level output voltage                            | VIL = 0.8 V,   | RL = 3 kΩ,  | V <sub>DD</sub> = 5 V, | $V_{SS} = -5 V$  | 4   | 4.5   |     | V    |
| VOH             | High-level output voltage                            | See Figure 1   |   | V <sub>DD</sub> = 12 V | $V_{SS} = -12 V$ | 10  | 10.8  |     | v    |
| Vei             | Low-level output voltage                             | VIH = 0.8 V,   | $R_L = 3 k\Omega$ ,   | V <sub>DD</sub> = 5 V, | $V_{SS} = -5 V$  |     | -4.4  | -4  | V    |
| VOL             | (see Note 3)   | See Figure 1   |   | V <sub>DD</sub> = 12 V | $V_{SS} = -12 V$ |     | -10.7 | -10 | v    |
| Iн              | High-level input current                             | V <sub>I</sub> = 5 V, See Figure 2                                   |   |                        |                  |     | 1     | μΑ  |      |
| ۱ <sub>IL</sub> | Low-level input current                              | V <sub>I</sub> = 0, See Figure 2                                     |   |                        |                  |     | -1    | μΑ  |      |
| IOS(H)          | High-level short-circuit output current (see Note 4) | $V_I = 0.8 V$ , $V_O = 0 \text{ or } V_O = V_{SS}$ ,<br>See Figure 1 |   |                        | -4.5             | -12 | -19.5 | mA  |      |
| IOS(L)          | Low-level short-circuit output current (see Note 4)  | $V_I = 2 V$ , $V_O = 0 \text{ or } V_O = V_{DD}$ ,<br>See Figure 1   |   |                        | 4.5              | 12  | 19.5  | mA  |      |
| r <sub>o</sub>  | Output resistance                                    | V <sub>DD</sub> = V <sub>SS</sub> =<br>See Note 5                    | $V_{DD} = V_{SS} = V_{CC} = 0,$ $V_O = -2 V \text{ to } 2 V,$<br>See Note 5 |                        |                  | 300 | 400   |     | Ω    |

<sup>†</sup> All typical values are at  $T_A = 25 \,^{\circ}C$ .

NOTES: 3. The algebraic convention, where the more positive (less negative) limit is designated as maximum, is used in this data sheet for logic levels only, e.g., if -10 V is a maximum, the typical value is a more negative voltage.

4. Not more than one output should be shorted at one time.

5. Test conditions are those specified by TIA/EIA-232-F.

# switching characteristics, $V_{DD}$ = 12 V, $V_{SS}$ = –12 V, $V_{CC}$ = 5 V $\pm 10\%,$ $T_A$ = 25°C (unless otherwise noted) (see Figure 3)

|                  | PARAMETER   |   | TEST CONDITIONS                          |  | TYP   | MAX | UNIT |    |
|------------------|---|---|--|--|---|-----|------|----|
| <sup>t</sup> PLH | Propagation delay time,<br>low- to high-level output (see Note 6) |   |  |  | 1.2   | 3   | μs   |    |
| <sup>t</sup> PHL | Propagation delay time,<br>high- to low-level output (see Note 6) | $R_L = 3 k\Omega \text{ to } 7 k\Omega$ , C | $R_L = 3 k\Omega$ to 7 kΩ, $C_L = 15 pF$ | $R_L = 3 k\Omega$ to 7 k $\Omega$ ,            | $R_L = 3 \text{ k}\Omega \text{ to } 7 \text{ k}\Omega,  C_L = 15 \text{ pF}$ | 2.5 | 3.5  | μs |
| <sup>t</sup> TLH | Transition time, low- to high-level output                        |   |  | 0.53   | 2   | 3.2 | μs   |    |
| <sup>t</sup> THL | Transition time, high- to low-level output                        |   |  | 0.53   | 2   | 3.2 | μs   |    |
| <sup>t</sup> TLH | Transition time, low- to high-level output (see Note 7)           |   |  | $R_{I} = 3 k\Omega$ to 7 kΩ, $C_{I} = 2500 pF$ |   | 1   |      | μs |
| <sup>t</sup> THL | Transition time, high- to low-level output (see Note 7)           | $\Gamma_{L} = 3 \times 2107 \times 22,$     | $O_{L} = 2500 \text{ pr}$                |  | 1   |     | μs   |    |
| SR               | Output slew rate (see Note 7)                                     | $R_L = 3 k\Omega$ to 7 kΩ,                  | C <sub>L</sub> = 15 pF                   | 4  | 10  | 30  | V/µs |    |

NOTES: 6. tpHL and tpLH include the additional time due to on-chip slew rate and are measured at the 50% points.

 Measured between 3-V and –3-V points of output waveform TIA/EIA-232-F conditions), and all unused inputs are tied either high or low.



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## **RECEIVER SECTION**

# electrical characteristics over operating free-air temperature range, $V_{DD}$ = 12 V, $V_{SS}$ = –12 V, $V_{CC}$ = 5 V $\pm 10\%$ (unless otherwise noted)

|                   | PARAMETER   |                           | TEST COND                 | ITIONS                  | MIN   | TYP†  | MAX  | UNIT |  |
|-------------------|---|---------------------------|---------------------------|-------------------------|-------|-------|------|------|--|
| VIT+              | Positive-going input threshhold voltage                             | See Figure 5              |                           |                         | 1.6   | 2.1   | 2.55 | V    |  |
| V <sub>IT</sub> – | Negative-going input threshhold voltage                             | See Figure 5              |                           |                         | 0.65  | 1     | 1.25 | V    |  |
| V <sub>hys</sub>  | Input hysteresis voltage<br>(V <sub>IT +</sub> - V <sub>IT</sub> _) |                           |                           |                         | 600   | 1100  |      | mV   |  |
|                   |   | V <sub>I</sub> = 0.75 V,  | $I_{OH} = -20 \ \mu A$ ,  | See Figure 5 and Note 8 | 3.5   |       |      |      |  |
| Varia             | High-level output voltage   | VI = 0.75 V,              | $V_{CC} = 4.5 V$          |                         | 2.8   | 4.4   |      |      |  |
| Vон               |   | $I_{OH} = -1 \text{ mA},$ | $V_{CC} = 5 V$            |                         | 3.8   | 4.9   |      | v    |  |
|                   |   | See Figure 5              | V <sub>CC</sub> = 5.5 V   |                         | 4.3   | 5.4   |      |      |  |
| VOL               | Low-level output voltage  | V <sub>I</sub> = 3 V,     | I <sub>OL</sub> = 3.2 mA, | See Figure 5            |       | 0.17  | 0.4  | V    |  |
|                   | High lovel input ourrest  | V <sub>I</sub> = 3 V      |                           |                         | 0.43  | 0.55  | 1    | mA   |  |
| IН                | High-level input current  | V <sub>I</sub> = 25 V     |                           |                         | 3.6   | 4.6   | 8.3  | mA   |  |
| l                 |   | V <sub>I</sub> = -3 V     |                           |                         | -0.43 | -0.55 | -1   | A    |  |
| ۱L                | Low-level input current   | V <sub>I</sub> = -25 V    |                           |                         | -3.6  | -5.0  | -8.3 | mA   |  |
| IOS(H)            | Short-circuit output at high level                                  | V <sub>I</sub> = 0.75 V,  | $V_{O} = 0,$              | See Figure 4            |       | -8    | -15  | mA   |  |
| IOS(L)            | Short-circuit output at low level                                   | $V_{I} = V_{CC},$         | $V_{O} = V_{CC},$         | See Figure 4            |       | 13    | 25   | mA   |  |

<sup>†</sup> All typical values are at  $T_A = 25 \,^{\circ}C$ .

NOTE 8: If the inputs are left unconnected, the receiver interprets this as an input low, and the receiver outputs remain in the high state.

## switching characteristics, $V_{DD}$ = 12 V, $V_{SS}$ = –12 V, $V_{CC}$ = 5 V $\pm 10\%,$ T\_A = 25°C (unless otherwise noted) (see Figure 6)

|                   | PARAMETER   |                        | TEST CONDITIONS        |                        | TYP                     | MAX | UNIT |     |    |
|-------------------|---|------------------------|------------------------|------------------------|-------------------------|-----|------|-----|----|
| <sup>t</sup> PLH  | Propagation delay time, low- to high-level output           | R <sub>L</sub> = 5 kΩ, | R <sub>L</sub> = 5 kΩ, | R <sub>L</sub> = 5 kΩ, |                         |     | 3    | 4   | μs |
| <sup>t</sup> PHL  | Propagation delay time, high- to low-level output           |                        |                        |                        | C <sub>I</sub> = 50 pF  |     | 3    | 4   | μs |
| t <sub>TLH</sub>  | Transition time, low- to high-level output                  |                        |                        |                        | $C_{L} = 30  \text{pr}$ |     | 300  | 450 | ns |
| <sup>t</sup> THL  | Transition time, high- to low-level output                  |                        |                        |                        | 100                     | 300 | ns   |     |    |
| <sup>t</sup> w(N) | Duration of longest pulse rejected as noise<br>(see Note 9) | $R_L = 5 k\Omega$ ,    | C <sub>L</sub> = 50 pF | 1                      |                         | 4   | μs   |     |    |

NOTE 9: The receiver ignores any postive- or negative-going pulse that is less than the minimum value of  $t_{W(N)}$  and accepts any positive- or negative-going pulse greater than the maximum of  $t_{W(N)}$ .



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## PARAMETER MEASUREMENT INFORMATION

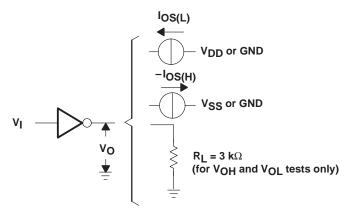


Figure 1. Driver Test Circuit for  $V_{OH}$ ,  $V_{OL}$ ,  $I_{OS(H)}$ , and  $I_{OS(L)}$ 

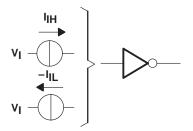


Figure 2. Driver Test Circuit for IIH and IIL

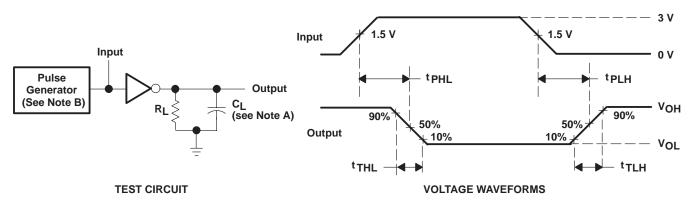




Figure 3. Driver Test Circuit and Voltage Waveforms



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#### PARAMETER MEASUREMENT INFORMATION

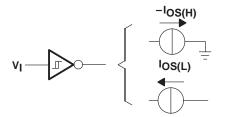


Figure 4. Receiver Test Circuit for IOS(H) and IOS(L)

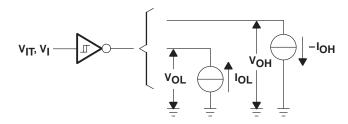
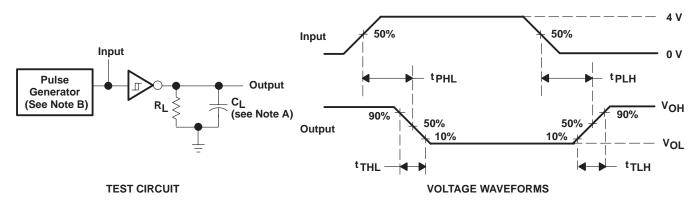
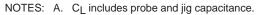


Figure 5. Receiver Test Circuit for VIT, VOH, and VOL



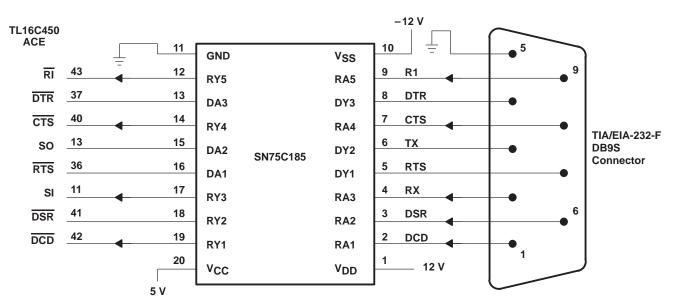


B. The pulse generator has the following characteristics:  $t_W$  = 25 µs, PRR = 20 kHz, Z<sub>O</sub> = 50 Ω,  $t_f$  =  $t_f$  < 50 ns.

#### Figure 6. Receiver Propagation and Transition Times



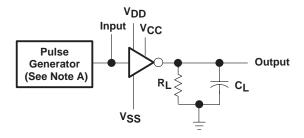
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#### **APPLICATION INFORMATION**



The SN75C185 supports data rates up to 120 kbit/s over a 3-meter cable. Laboratory experiments show that, with  $C_L$ = 500 pF and  $R_L$  = 3 k $\Omega$  (minimum RS-232 input resistance load), the device can support this data rate. The 500-pF load approximates a typical 3-meter cable because the maximum RS-232 specification is 2500 pF (or about 15 meters). Figure 8 shows the test circuit used. Temperature was varied from 0°C to 70°C for the experiment.



NOTES: A. The pulse generator has the following characteristics: PRR = 60 kHz (120 kbit/s),  $Z_O = 50 \Omega$ . B.  $V_{CC} = 5 V$ ,  $V_{DD} = 12 V$ ,  $V_{SS} = -12 V$ .

#### Figure 8. Data-Rate Test Circuit



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